

EUV and e-beam exposures of Ru-capped multilayer mirrors

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Degradation of EUV projection optics

Industry Problem

Lifetime of Mo-Si multi-layer mirrors (MLM) under anticipated projection-tool conditions *much* too short.

Requirements: $\Delta R < 1-2\%$ over 30,000 hr lifetime

Conditions: EUV intensity, $I_{\text{EUV}} = 10 \text{ mW/mm}^2$
Unbaked vacuum, $P_{\text{H}_2\text{O}} \sim 2 \times 10^{-7} \text{ Torr}$

NIST/Sandia Goal

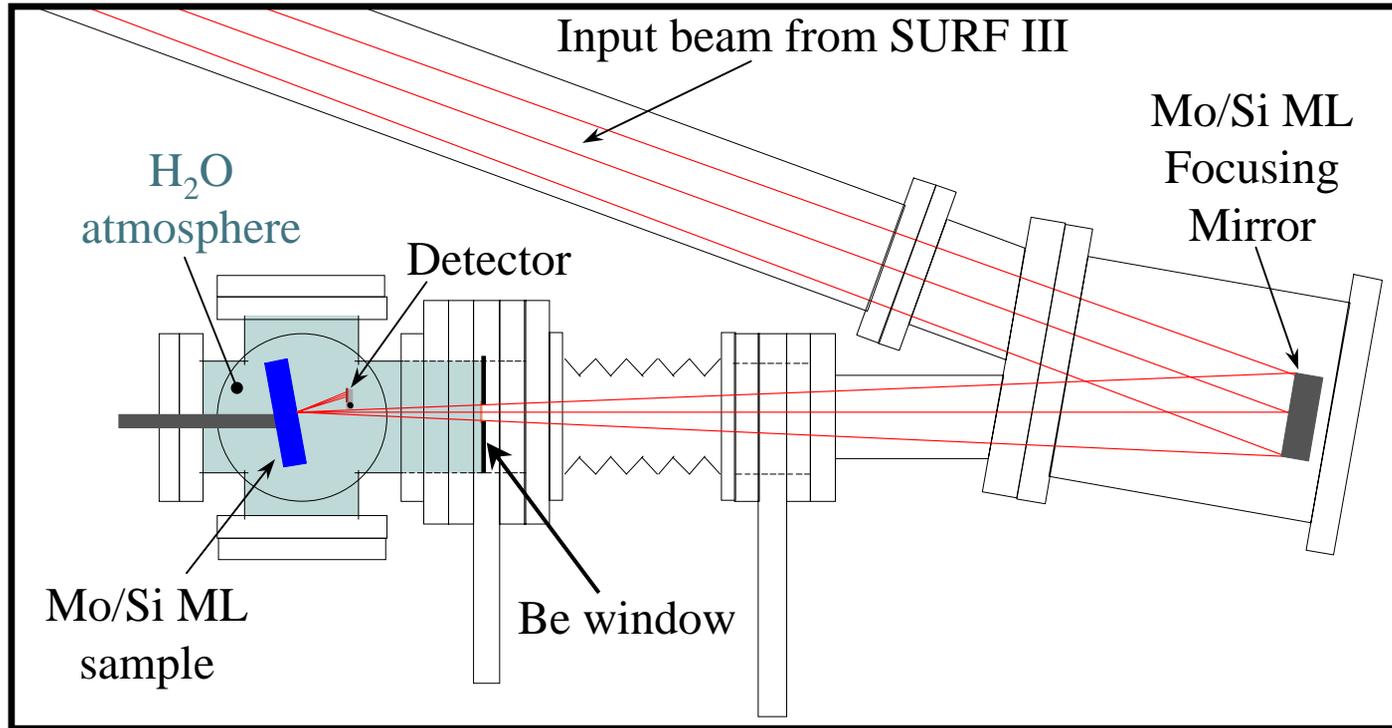
Develop metrology techniques to estimate lifetime of new, more robust MLs under anticipated projection-tool conditions.

- Find scaling laws relating ΔR to I_{EUV} , $P_{\text{H}_2\text{O}}$, and T_{Exposure}
- Predict ML lifetime in tool ($\sim 10^4$ hrs) from $\sim 10^2$ hrs of accelerated testing under aggressive I_{EUV} and $P_{\text{H}_2\text{O}}$ conditions

Outline

- EUV and e-beam exposure conditions
- Oxide growth on Si-cap ML for EUV and e-beam exposures
- Reflectivity decrease, ΔR , for Ru-cap ML exposed to EUV and e-beam
- Correlation of oxide thickness and ΔR for Ru-cap ML
- Development of sensitive *in situ* monitor of ΔR

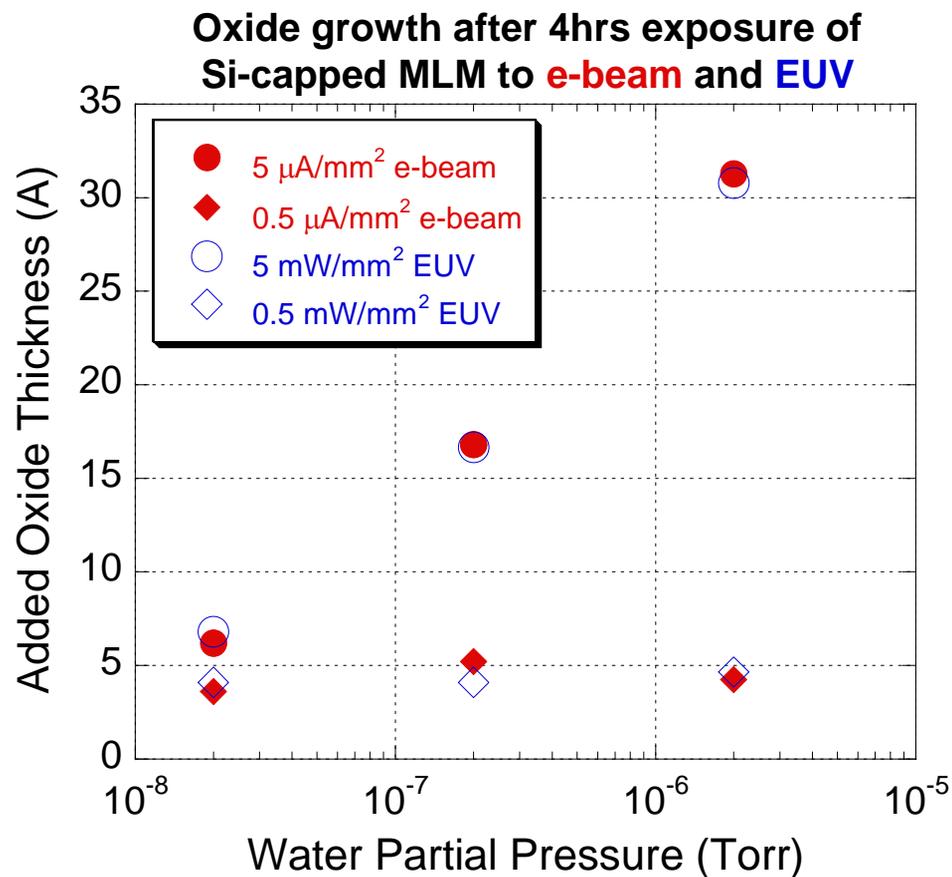
EUV Exposures at NIST



- Spot size $\sim 600 \mu\text{m} \times 850 \mu\text{m}$ (FWHM) at sample
- Average, in-band (13.0-13.5nm) intensity $\sim 5 \text{ mW}/\text{mm}^2$
- Be window permits large water vapor pressures: $P_{\text{H}_2\text{O}} = 10^{-5} \text{ Torr}$
- Detect large reflectivity changes *in situ* with photodiode

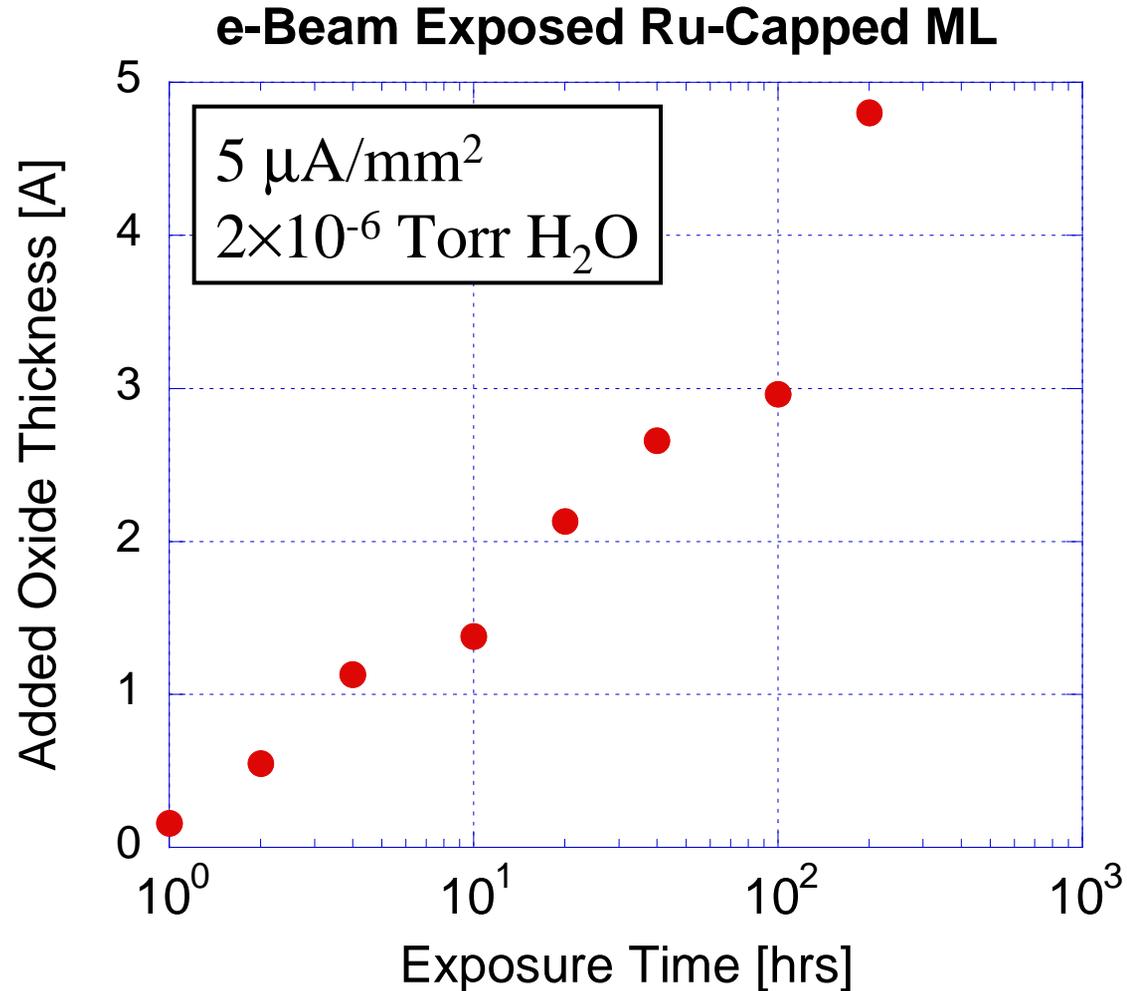
Electron-beam Exposures at Sandia

- Reflectivity decrease of Si-cap ML correlated to SiO_2 growth
- Equal oxide growth on Si-cap ML exposed to:
 - **1 $\mu\text{A}/\text{mm}^2$ 1 keV e-beam**
 - **1 mW/mm^2 13 nm EUV**
- e-beam is convenient proxy for EUV exposure of Si-capped ML



Decreased Oxide Growth on Ru-capped ML

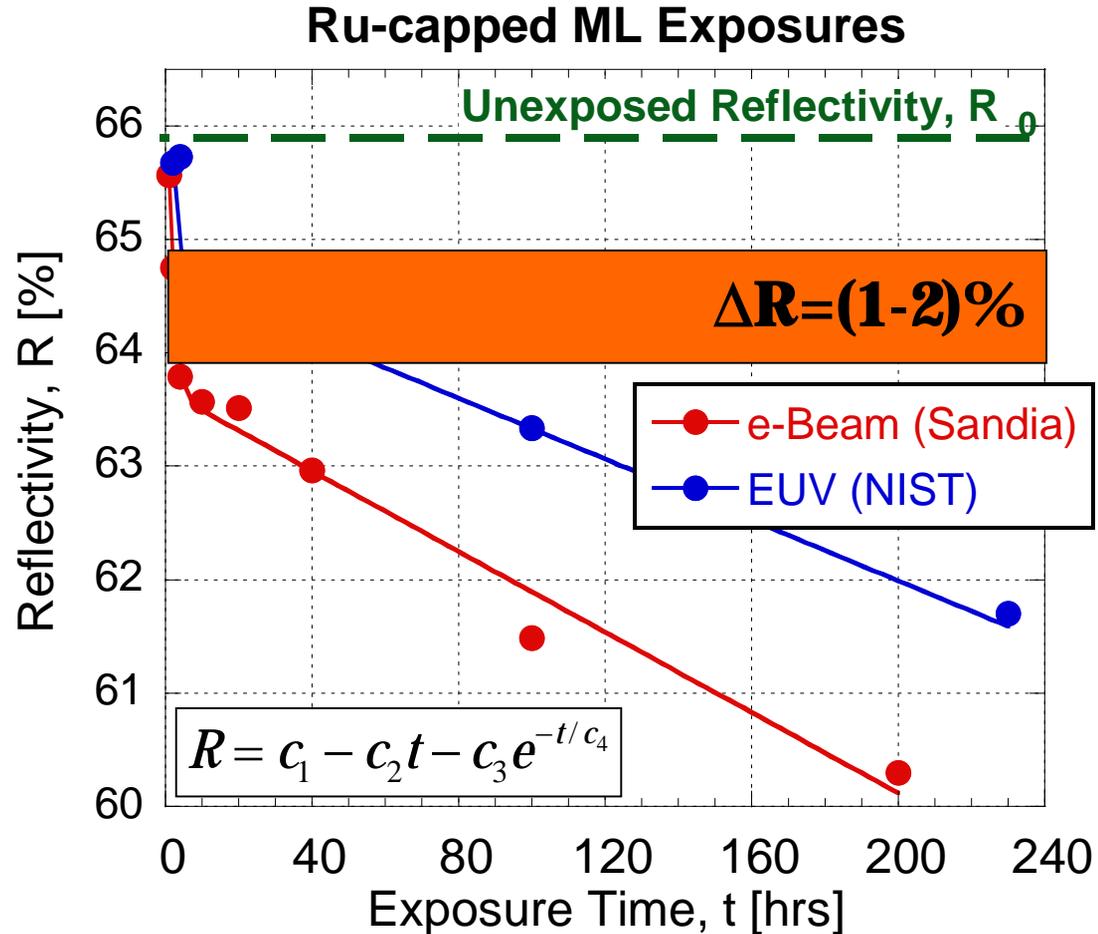
- Si-cap ML added **20Å** oxide after only 4hrs
- Auger measurements for EUV exposures underway...
- Ru-cap appears ~20x more resistant than Si-cap



Reflectivity Degradation of Ru-capped ML

- Exposure conditions:
 - 5 $\mu\text{A}/\text{mm}^2$ e-beam
 - 5 mW/mm^2 EUV
 - 2×10^{-6} Torr H_2O

• 1 mW/mm^2 EUV ***not*** equivalent to 1 $\mu\text{A}/\text{mm}^2$ e-beam for Ru-cap ML



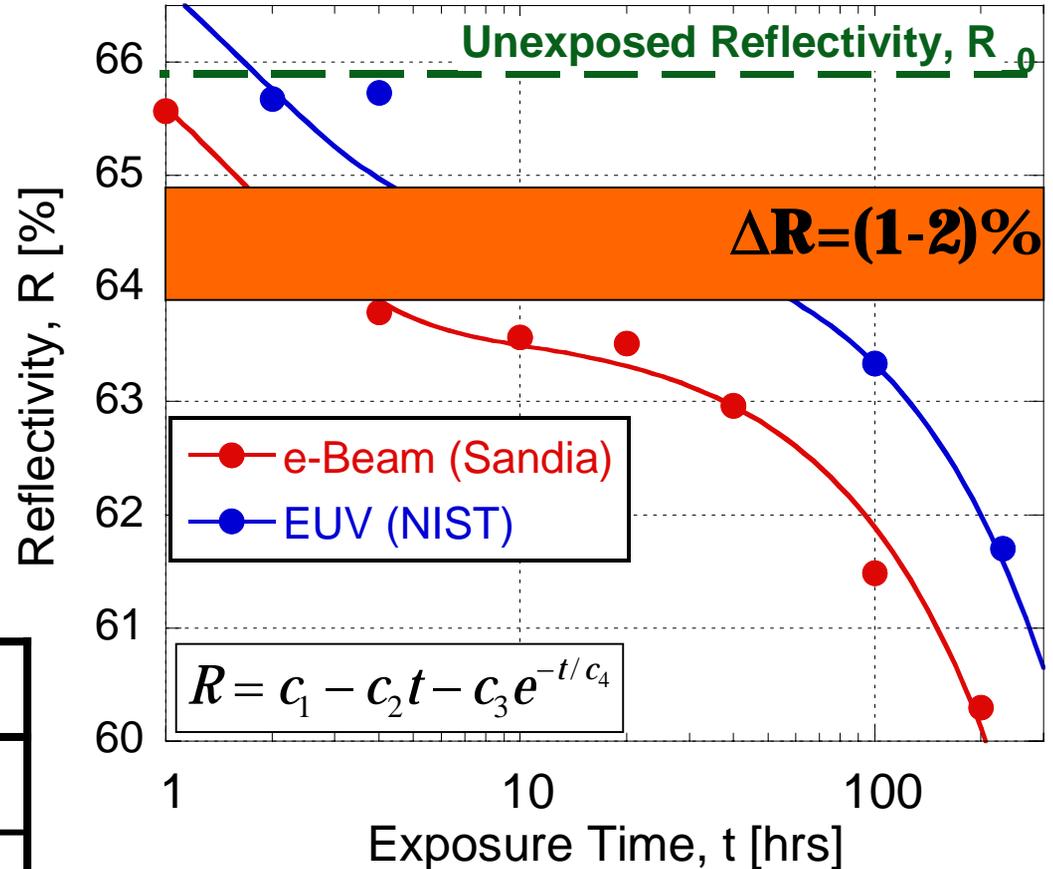
Reflectivity Degradation of Ru-capped ML

- Exposure conditions:
 - 5 $\mu\text{A}/\text{mm}^2$ e-beam
 - 5 mW/mm^2 EUV
 - 2×10^{-6} Torr H_2O

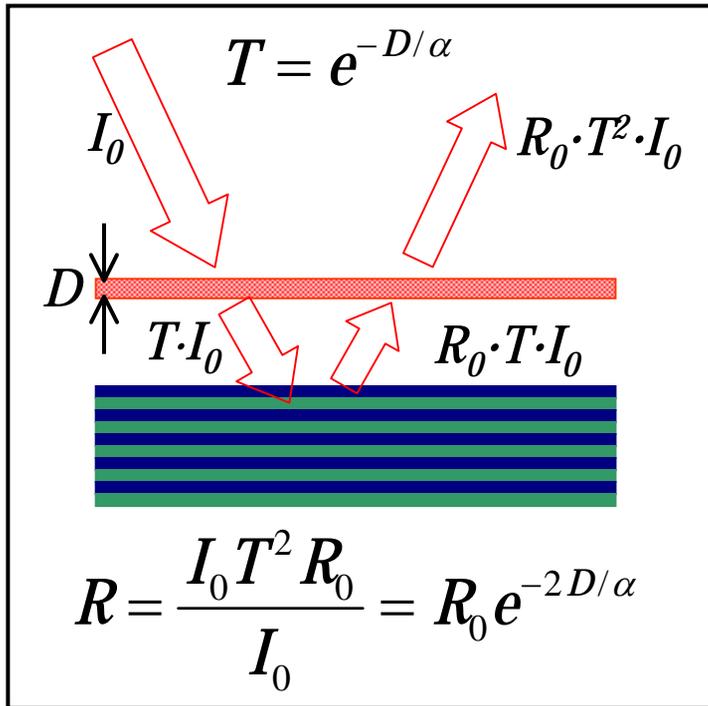
• 1 mW/mm^2 EUV **not** equivalent to 1 $\mu\text{A}/\text{mm}^2$ e-beam for Ru-cap ML

ΔR	EUV	e-beam
1%	~4 hrs	=2 hrs
2%	60 hrs	~4 hrs

Ru-capped ML Exposures



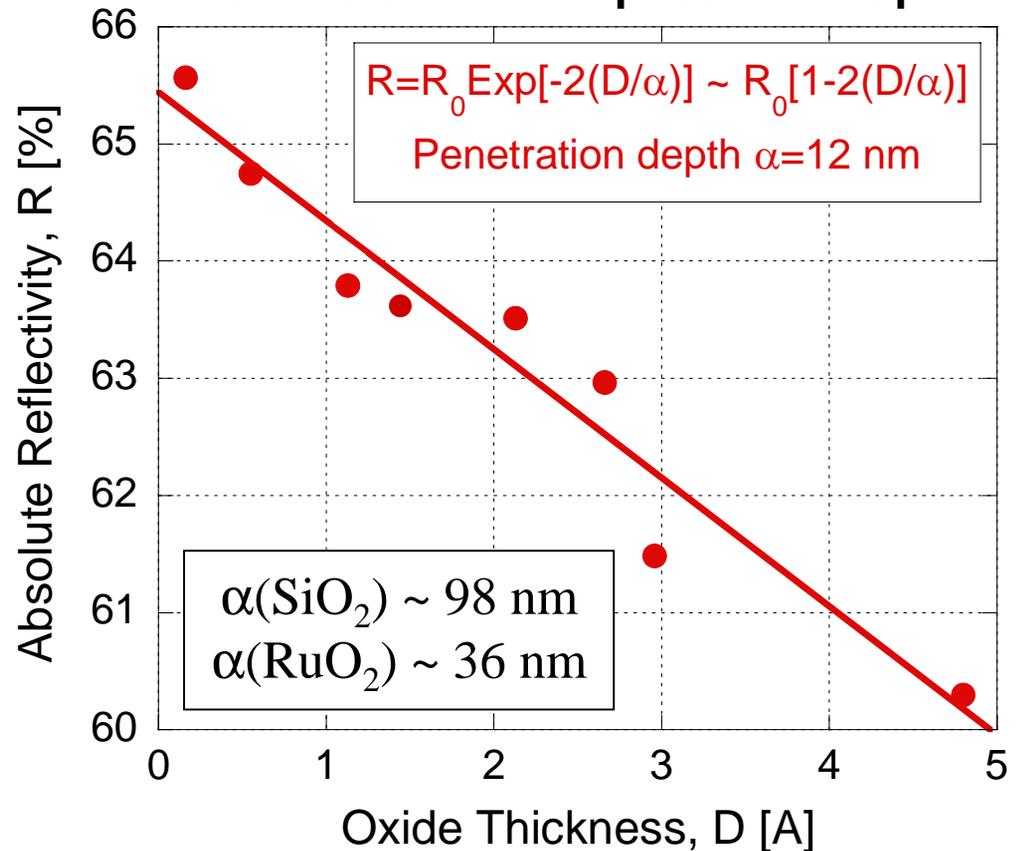
Ru-cap ML Reflectivity and Oxide Thickness



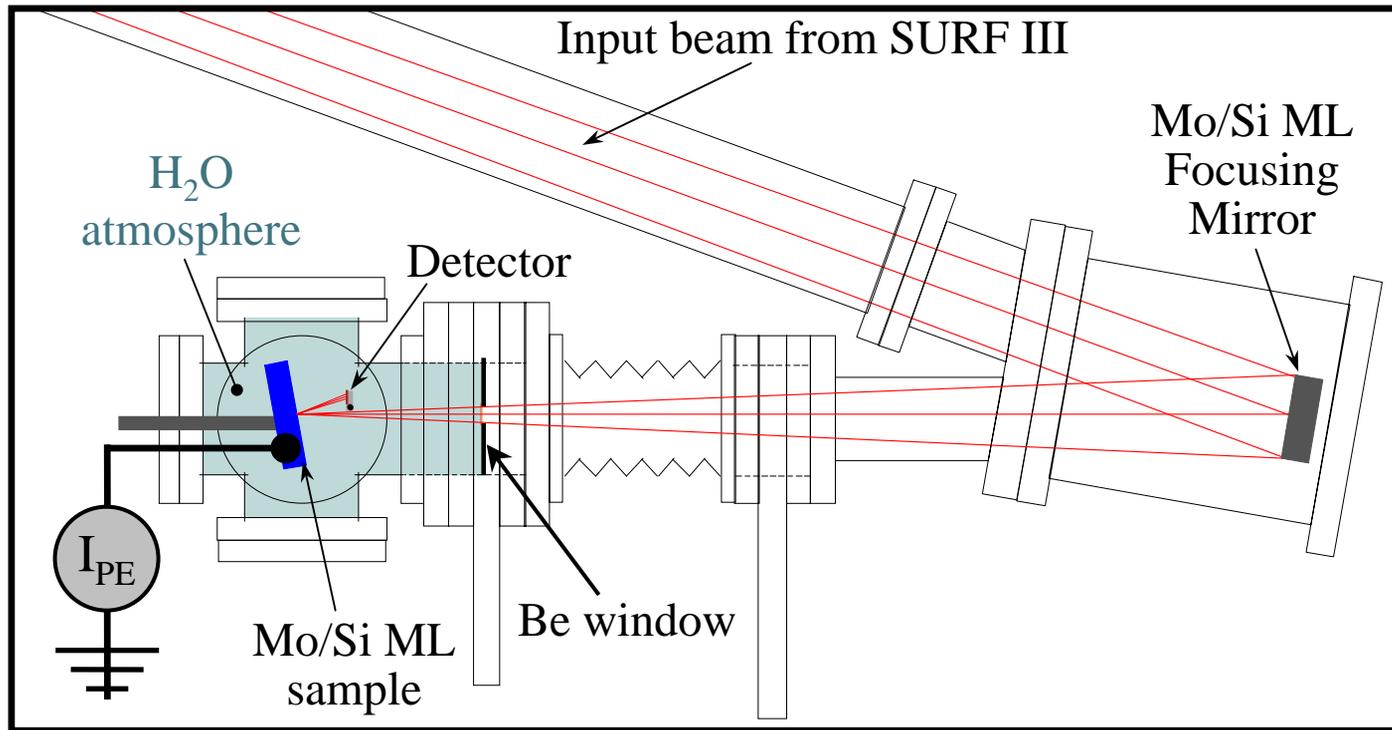
Attenuation of added oxide
not primary cause of ΔR .

Interfacial roughening?
Diffusion?

Effective Penetration Depth of Oxide
Added to e-Beam Exposed Ru-cap ML



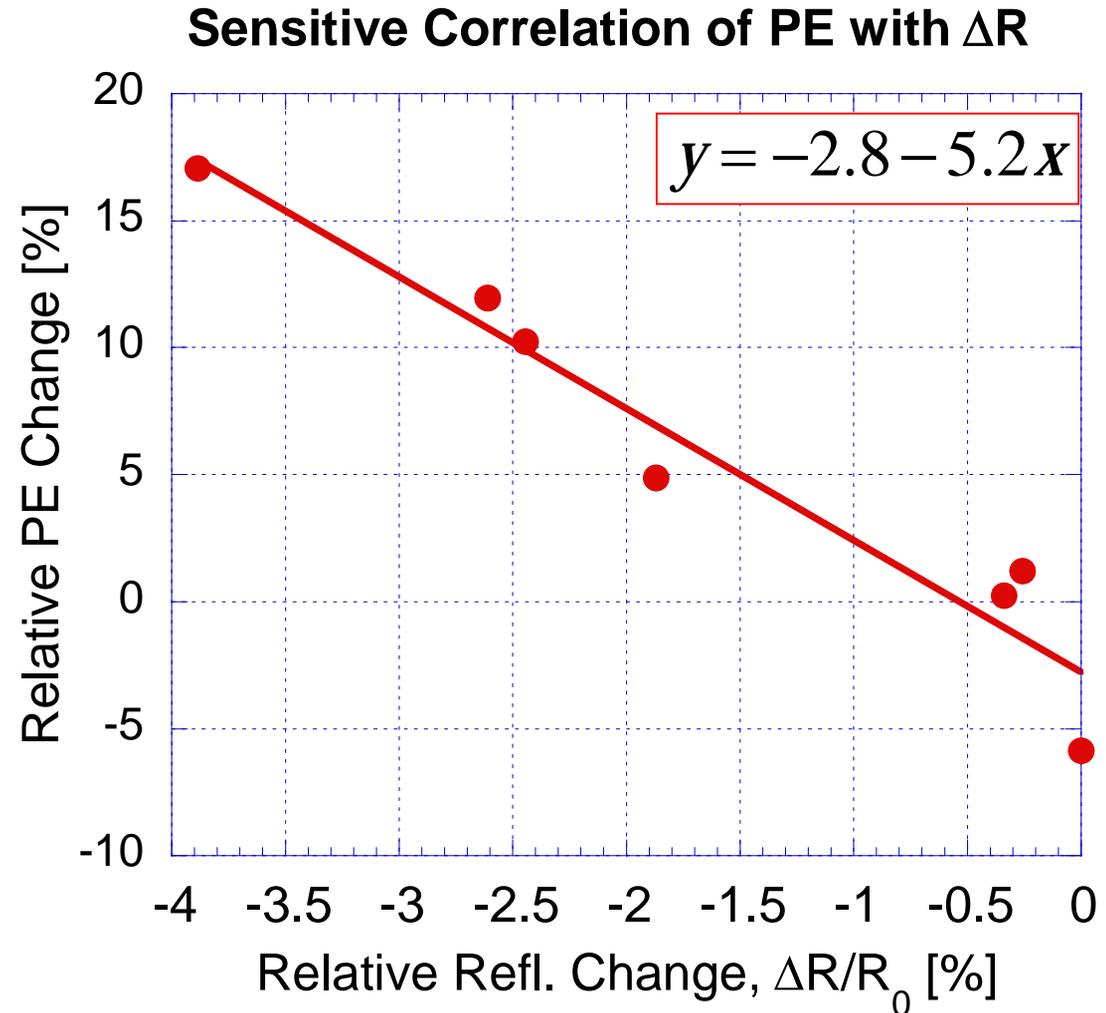
Precise *in situ* ΔR Measurements Difficult



- Measured *integrated* (13.0-13.5nm) reflectivity $R_{int} < 45\%$
- Need reproducibility $< 0.5\%$ (absolute) for R_{int} measurements
- Could photoemission current (I_{PE}) be indicator of ΔR @ 13.4nm?

Reflectivity and Photoemission Changes Correlated

- Compare *in situ* PE with ALS measured ΔR @ 13.4nm
- A 1% relative ΔR produces a 5.2% change in PE
- PE may serve as sensitive *in situ* proxy for ΔR @ 13.4nm.



Conclusions

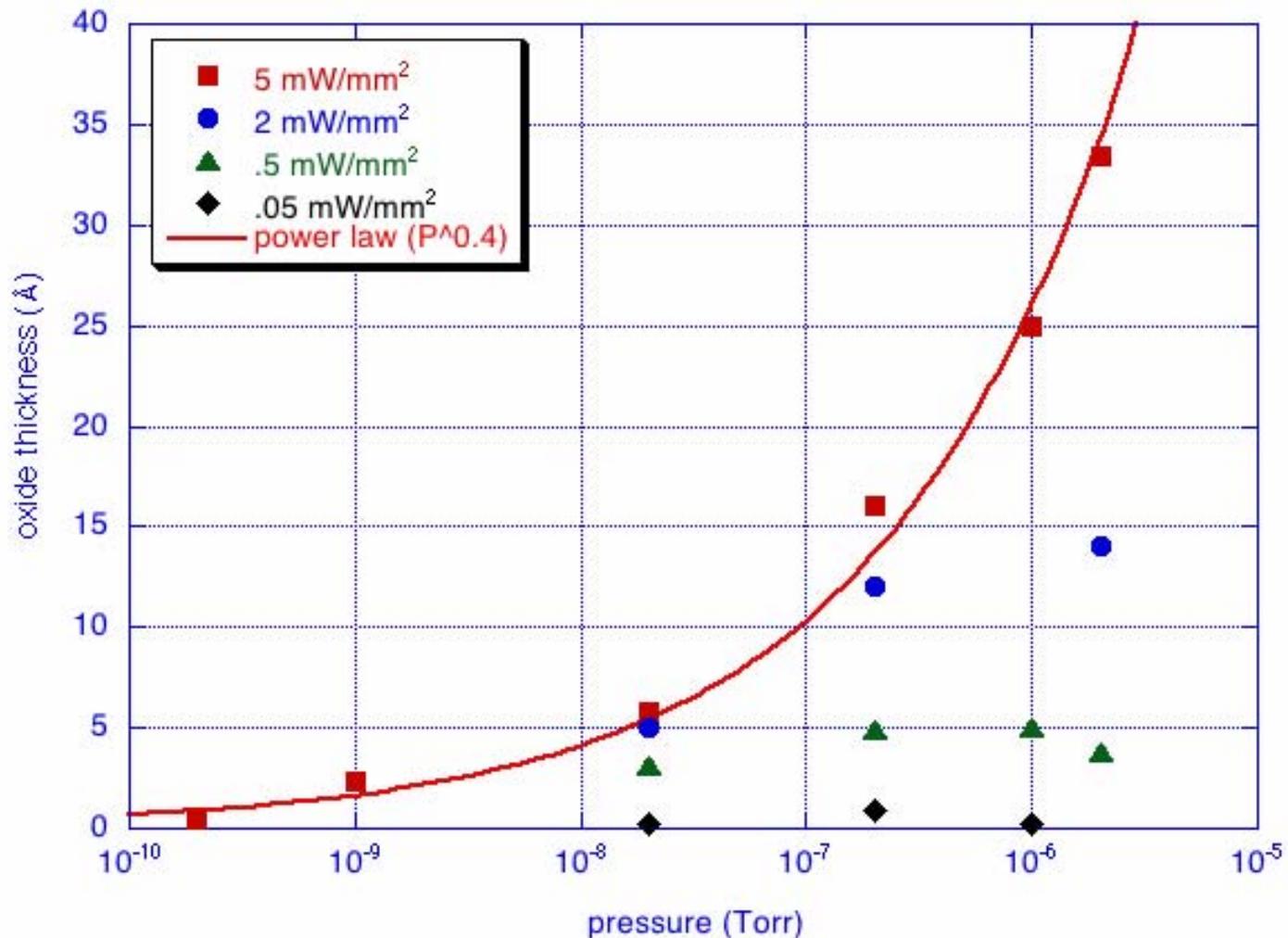
- Equivalence between e-beam and EUV exposures is different for Ru- and Si-capped MLs:
 ΔR (1 mW/mm² EUV) < ΔR (1 μ A/mm² e-beam)
- 1% ΔR occurs after ~4 hrs of EUV exposure
2% ΔR occurs after ~60 hrs of EUV exposure

Future Plans

- Develop photoemission current as *in situ* monitor of ΔR with sensitivity to detect 1% relative changes during EUV exposures.
- Expose Ru-cap ML over range of H₂O pressures and EUV/e-beam intensities to determine scaling behavior of ΔR .

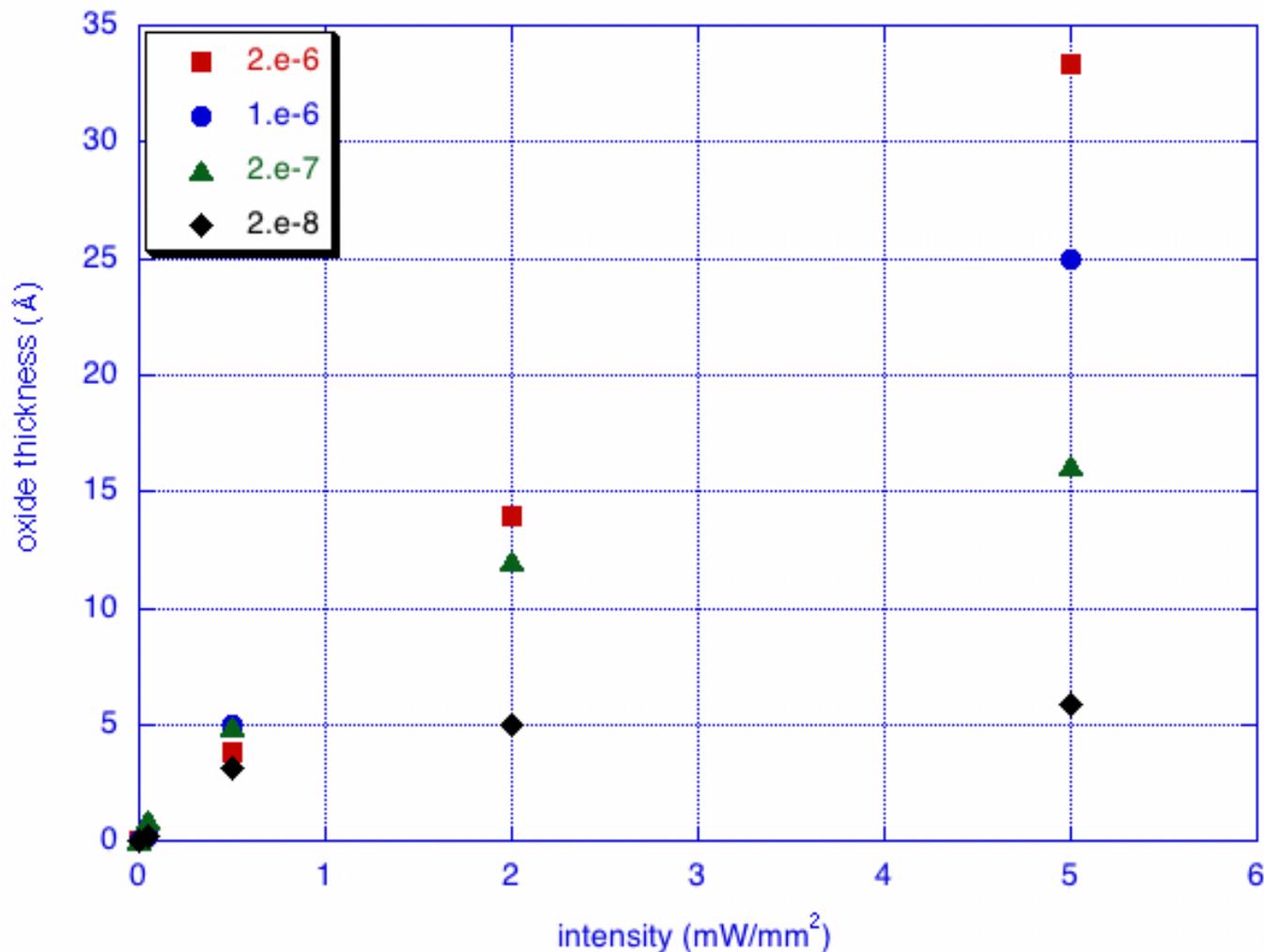
Photon Limited Oxidation of Si-cap ML

4hr EUV & e-beam exposures



H₂O Limited Oxidation of Si-cap ML

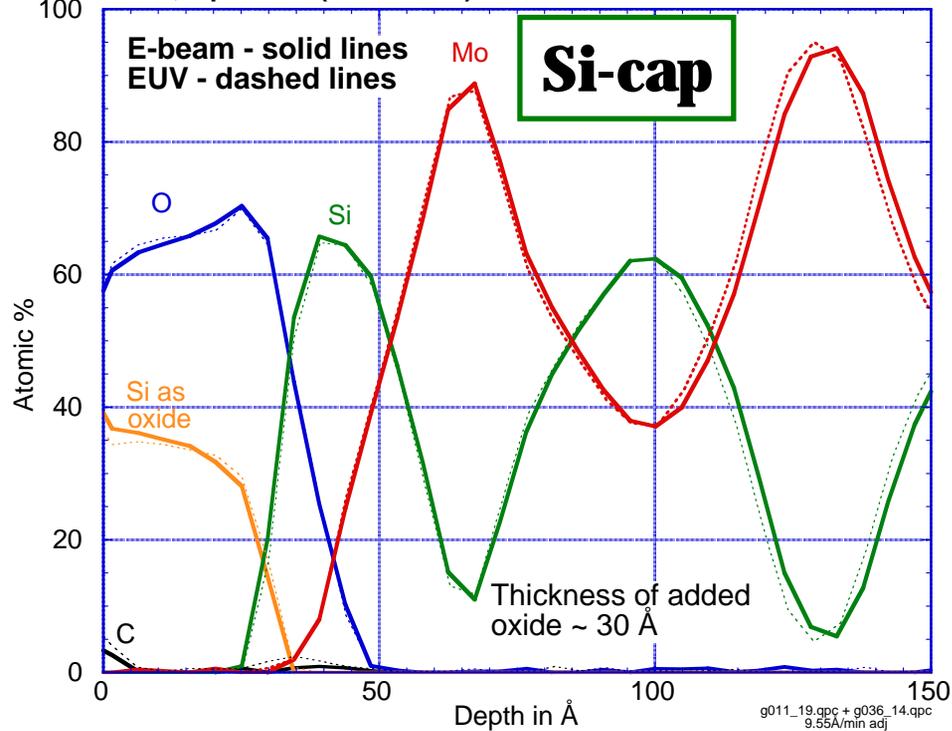
4hr EUV & e-beam exposures



Auger depth profiles: 4hr e-beam exposures of Si- & Ru-capped MLs

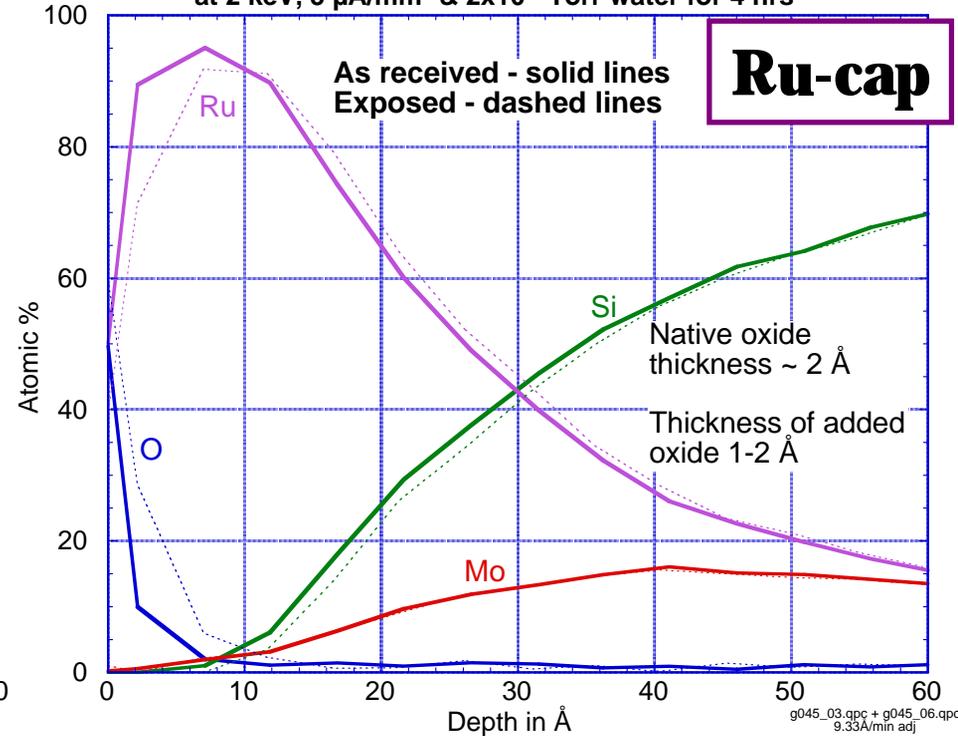
Si Capped MLM M3-030408B1D

2 keV, 5 $\mu\text{A}/\text{mm}^2$ (5 mW/mm²) & 2 x 10⁻⁶ Torr Water for 4 hrs



Ru Capped Prep 1 MLM (M3-030918A1A) Exposed to E-beam

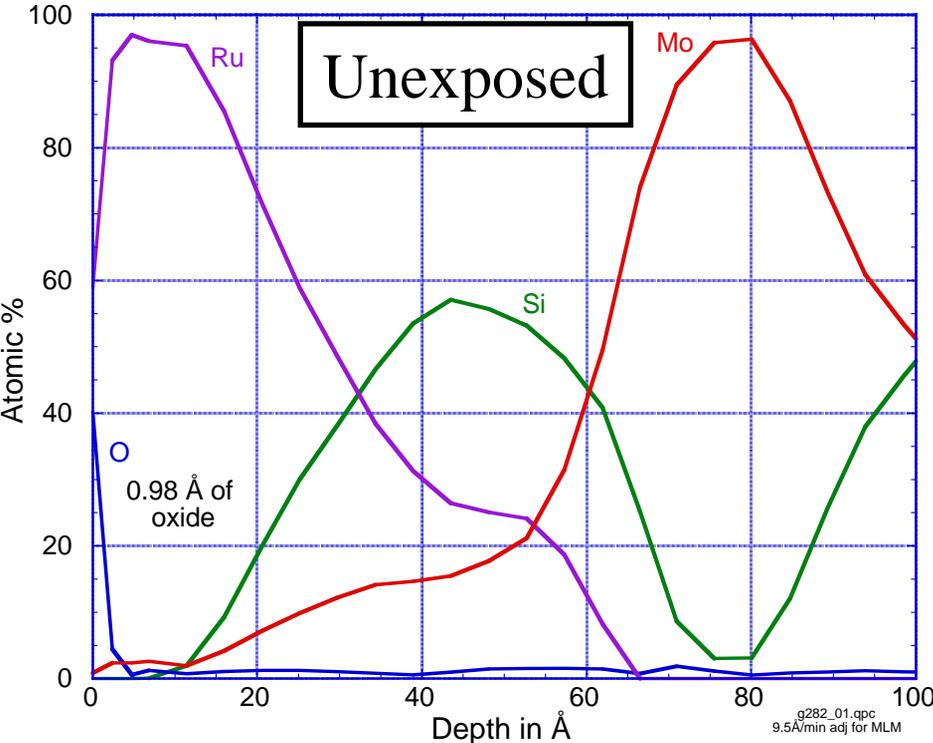
at 2 keV, 5 $\mu\text{A}/\text{mm}^2$ & 2x10⁻⁶ Torr water for 4 hrs



Auger depth profile of 100hr e-beam exposure of Ru-capped ML

M3-030917A11 Prep 1, Unexposed Area

Unexposed



M3-030917A11 Prep 1, 100-Hour Exposed Area at 1.5 keV 5 $\mu\text{A}/\text{mm}^2$ and 2×10^{-6} Torr Water

100 hr e-beam

